# Single Schmitt-Trigger Buffer

The NL17SH17 is a single gate CMOS Schmitt-trigger non-inverting buffer fabricated with silicon gate CMOS technology. The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The NL17SH17 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the NL17SH17 to be used to interface 5 V circuits to 3 V circuits.

The NL17SH17 can be used to enhance noise immunity or to square up slowly changing waveforms.

#### **Features**

- High Speed:  $t_{PD} = 4.0 \text{ ns}$  (Typ) at  $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1.0 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 101
- These Devices are Pb-Free and are RoHS Compliant

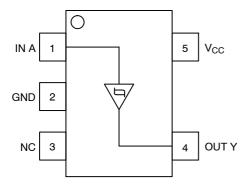


Figure 1. Pinout



Figure 2. Logic Symbol



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MARKING DIAGRAM



SOT-953 CASE 527AE



Y = Specific Device Code (Rotated 90°)

M = Month Code

PIN ASSIGNMENT					
1	IN A				
2	GND				
3	NC				
4	OUT Y				
5	V <sub>CC</sub>				

#### **FUNCTION TABLE**

Input A	Output Y
L	L
Н	н

# ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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#### **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-20	mA
lok	DC Output Diode Current	V <sub>OUT</sub> < GND, V <sub>OUT</sub> > V <sub>CC</sub>	±20	mA
l <sub>out</sub>	DC Output Source/Sink Current		±12.5	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±25	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±25	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Secon	ds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>3000 >200 N/A	V
I <sub>LATCHUP</sub>	Latchup Performance Above V <sub>C</sub>	<sub>CC</sub> and Below GND at 125°C (Note 5)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Mi	n	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage	1.6	55	5.5	V
V <sub>IN</sub>	Digital Input Voltage	0.0	0	5.5	V
V <sub>OUT</sub>	Output Voltage	0.0	0	$V_{CC}$	V
T <sub>A</sub>	Operating Temperature Range	-5	5	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate $V_{CC} = 3.3 \text{ V} = 0.00 \text{ V}$	± 0.3 V ± 0.5 V 0		No Limit No Limit	ns/V

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

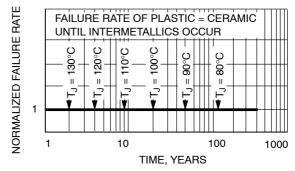


Figure 3. Failure Rate vs. Time Junction Temperature

#### DC ELECTRICAL CHARACTERISTICS

			v <sub>cc</sub>	1	T <sub>A</sub> = 25°(	)	T <sub>A</sub> ≤	85°C	-55°C 1	to 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>T+</sub>	Positive Threshold Voltage		3.0 4.5 5.5		2.0 3.0 3.6	2.2 3.15 3.85		2.2 3.15 3.85		2.2 3.15 3.85	V
V <sub>T-</sub>	Negative Threshold Voltage		3.0 4.5 5.5	0.9 1.35 1.65	1.5 2.3 2.9		0.9 1.35 1.65		0.9 1.35 1.65		V
V <sub>H</sub>	Hysteresis Voltage		3.0 4.5 5.5	0.3 0.4 0.5	0.57 0.67 0.74	1.2 1.4 1.6	0.3 0.4 0.5	1.2 1.4 1.6	0.3 0.4 0.5	1.2 1.4 1.6	V
V <sub>OH</sub>	High-Level Output Voltage	$V_{IN} \ge V_{Tmin}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		٧
		$V_{IN} \geq V_{Tmin}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Low-Level Output Voltage	$V_{IN} \le V_{Tmax}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	٧
		$V_{IN} \leq V_{Tmax}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		±1.0		±1.0	μΑ
Icc	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			1.0	_	20		40	μА

# AC ELECTRICAL CHARACTERISTICS (Input $t_{\text{f}} = t_{\text{f}} = 3.0 \text{ ns}$ )

		V <sub>cc</sub>	Test	1	Γ <sub>A</sub> = 25°C	<b>)</b>	T <sub>A</sub> ≤	85°C	−55°C t	to 125°C	
Symbol	Parameter	(V)	Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, A to Y	3.0 to 3.6	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.0 8.5	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	17.0 20.5	ns
		4.5 to 5.5	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.0 5.5	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	11.5 13.5	
C <sub>IN</sub>	Input Capacitance				5.0	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	7.0	pF

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

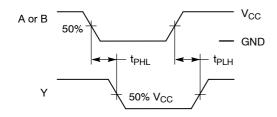
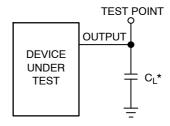


Figure 4. Switching Waveform



\*Includes all probe and jig capacitance.

Figure 5. Test Circuit

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NL17SH17P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel

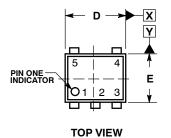
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

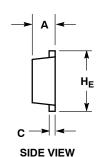


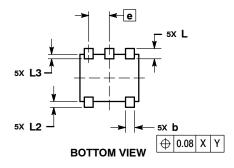
SOT-953 CASE 527AE **ISSUE E** 

**DATE 02 AUG 2011** 

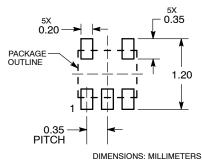








#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF THE BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS						
DIM	MIN	NOM	MAX				
Α	0.34	0.37	0.40				
b	0.10	0.15	0.20				
С	0.07	0.12	0.17				
D	0.95 1.00		1.05				
E	0.75	0.80	0.85				
е		0.35 BS	С				
HE	0.95	1.00	1.05				
L	0.175 REF						
L2	0.05	0.10	0.15				
L3			0.15				

#### **GENERIC MARKING DIAGRAM\***



= Specific Device Code = Month Code

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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